



Features

- Wide range of operating supply voltage: 2.2V to 5.5V
- Optimized low crystal drive current oscillation for miniature crystal units
- XO5009ALx-C-V series: for Wire Bonding
- Recommended oscillation frequency range
- Low frequency Fundamental: 10MHz to 60MHz
- Multi-stage frequency divider for low-frequency output support
- High Performance(Low Phase Noise/Low Jitter)
- High Frequency VS Vdd Stability $< \pm 1$ ppm
- Ultra-Low Drive Level
- Ultra-low Power Current
- Frequency divider built-in:
-Selectable by version: f_0 , $f_0/2$, $f_0/4$, $f_0/8$
- -55 to 125°C operating temperature range
- 50pF output drive capability
- Standby function
- High impedance in standby mode, oscillator stops
- CMOS output duty level($1/2V_{DD}$)
-50±5% output duty
- Die form or Wafer form
- AEC-Q 100 qualified. PPAP capable, and manufactured in IATF 16949 certified facilities.

Description

The XO5009ALx-C-V series are miniature crystal oscillator module ICs. The oscillator circuit stage has voltage regulator drive, significantly reducing current consumption and crystal current, compared with existing devices, and significantly reducing the oscillator characteristics supply voltage dependency.

Application

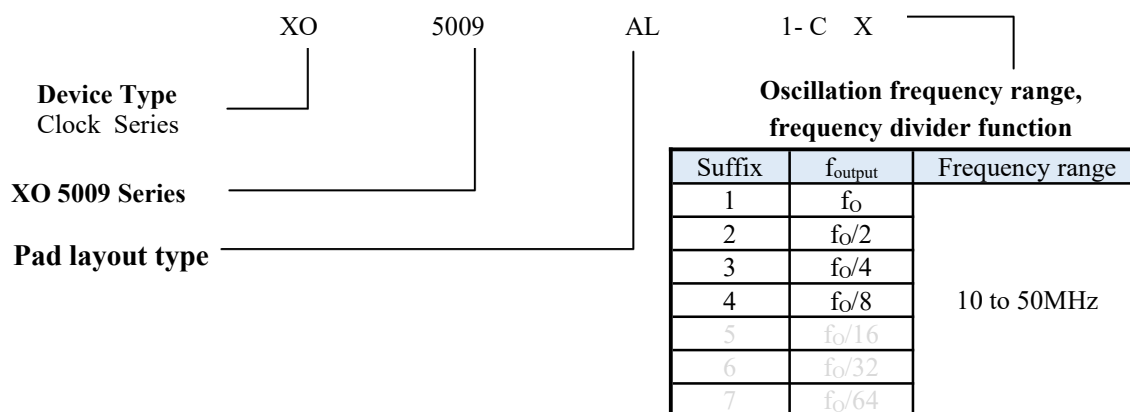
- Used for crystal oscillator
- 7050, 5032 Crystal Oscillator
- 3225, 2520, Crystal Oscillator

Ordering Information

Part no.	Package type
XO5009ALx-zWF-C-V	Wafer form
XO5009ALx-zDE-C-V	Die form

Note: 1. Below is the detailed definition of part no.

Note: 2. xx:3/4, z: -3(130um), -4(100um)



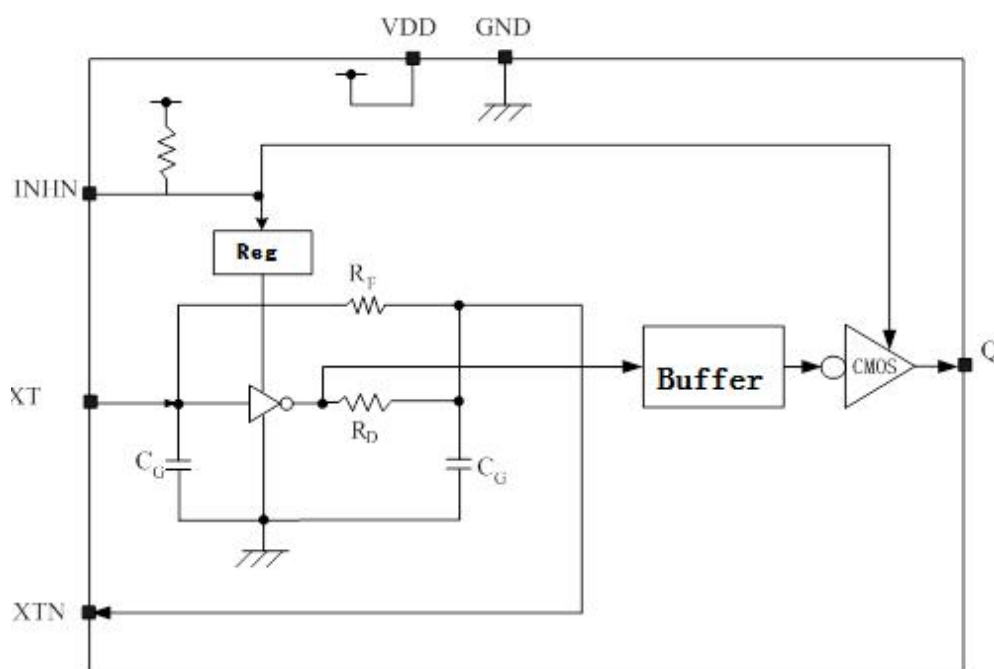
X: 3 Stand for 130um die thickness
4 Stand for 100um die thickness



Series Configuration

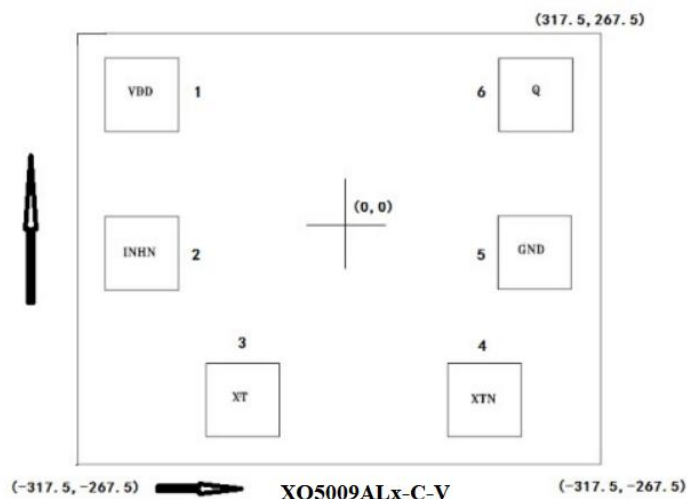
Part No.	Output frequency	Operating supply voltage range(V)	Oscillation mode	Recommended oscillation frequency range ^{*1} (MHz)	Output drive capability(mA)	Standby mode	
						Oscillator stop function	Output state
XO5009AL1-C-V	f_0	2.2~5.5	Fundamental	10 to 50	16	Yes	Hi-Z
XO5009AL2-C-V	$f_0/2$						
XO5009AL3-C-V	$f_0/4$						
XO5009AL4-C-V	$f_0/8$						
XO5009AL5 ^{*2}	$f_0/16$						
XO5009AL6 ^{*2}	$f_0/32$						
XO5009AL7 ^{*2}	$f_0/64$						

Block Diagram





Pad Configuration



Pad Coordinate File					
Pad Name	X Coordinate	Y Coordinate	Pad Name	X Coordinate	Y Coordinate
1	-214.85	168	4	158.35	-164.6
2	-214.85	-4.65	5	213.15	-3.85
3	-105.1	-164.6	6	214.2	167.9
Note: Substrate is connected to GND or floating.					
Die Size: 630μm*530μm (Including scribe line , Scribe Line Width 60um)					
Die Thickness: 130μm±15μm(-3) , 100um±15um(-4)					
Pad Size: 80μm*80μm			Substrate Level: GND or Floating		

Pad Description

Sym.	Type	Description	
XTN	O	Amplifier output.	Crystal connected between XT and XTN
XT	I	Amplifier input.	
INHN	I	Output state control input. High impedance when LOW. Power-saving pull-up resistor built in.	
V _{DD}	P	Supply voltage	
GND	P	Ground	
Q	O	Output. Output frequency determined by internal circuit to one of f _o ,f _o /2,f _o /4,f _o /8	



Function Description

Standby Function

When INHN goes LOW, the oscillator stops and the output on Q becomes high impedance.

INHN	Q	Oscillator
HIGH (or open)	f_o output frequency	Normal operation
Low	High impedance	Stopped

Power-saving Pull-up Resistor

The INHN pin pull-up resistance RUP1 or RUP2 changes in response to the input level(HIGH or LOW). When INHN is tied LOW level, the pull-up resistance is large(RUP1),reducing the current consumed by the resistance. When INHN is left open circuit, the pull-up resistance is small(RUP2),which increases the input susceptibility to external noise. However, the pull-up resistance ties the INHN pin HIGH level to prevent external noise from unexpectedly stopping the output.

Oscillation Detector Function

The XO5009ALx-C-V series also feature an oscillation detector circuit. This circuit functions make the outputs disable until the oscillator circuit starts and oscillation becomes stable. This alleviates the danger of abnormal oscillator output at oscillator start-up when power is applied or when INHN is switched.



Maximum Ratings

Storage Temperature.....	- 65°C to +150°C
Supply Voltage to Ground Potential (V _{DD} to GND).....	-0.5V to +7.0V
DC Input (All Other Inputs except V _{DD} & GND).....	-0.5V to V _{DD} +0.5V
DC Output.....	-0.5V to V _{DD} +0.5V
DC Output Current (all outputs).....	20mA

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Recommended Operating Conditions

(GND=0V, unless otherwise noted.)

Sym.	Parameter	Series	Conditions	Min	Typ	Max	Unit
V_{DD}	Supply voltage	All series	$C_L = 15\text{pF}$	2.2	-	5.5	V
V_{IN}	Input voltage	All series	-	GND	-	V_{DD}	V
T_A	Operating temperature	All series	-	-55	-	+125	°C
f_o	Oscillation frequency*1	5009x1-5009x4	$V_{DD} = 2.2\text{V} \sim 5.5\text{V}$ -	10	-	50	MHz
f_{OUT}	Output frequency	5009x1-5009x4	$V_{DD} = 2.2\text{V} \sim 5.5\text{V}$	-	-	50	MHz

Reliability Data

Sym.	Parameter	Series	Conditions	Min	Typ	Max	Unit
ESD	Human Body Model	All series	MIL-STD-883H Method 3015.8	+/-3000	+/-7500		V

Note: Industrial Standard ESD: HBM Model +/-2000V



DC Electrical Characteristics

XO5009AL1-C-V to XO5009AL6-C-V ($V_{DD} = 2.5$ to $5.5V$, $T_A = -40$ to $85^{\circ}C$, unless otherwise noted.)

Sym.	Parameter	Condition		Rating			Unit
				min	typ	max	
V _{OH}	HIGH-level output voltage	Q: Measurement cct3, I _{OH} =8mA		V _{DD} -0.4	-	-	V
V _{OL}	LOW-level output voltage	Q: Measurement cct3, I _{OL} =8mA		-	-	0.4	V
V _{IH}	HIGH-level input voltage	INH, Measurement cct4		0.7V _{DD}	-	-	V
V _{IL}	LOW-level input voltage	INH, Measurement cct4		-	-	0.3V _{DD}	V
I _Z	Output leakage current	Q: Measurement cct5, IHNH=LOW	V _{OH} =V _{DD}	-	-	10	uA
			V _{OL} =GND	-	-	10	uA
I _{DD}	Current consumption	Measurement cct 1, 5009AL1-C-V(f ₀),no load INH=open,f ₀ =24MHz	V _{DD} =2.5V	-	0.8	1.6	mA
			V _{DD} =3.3V	-	1.1	2.0	mA
			V _{DD} =5.0V	-	1.4	2.8	mA
		Measurement cct 1, 5009AL2-C-V(f ₀ /2),no load INH=open,f ₀ =24MHz f _{OUT} =12MHz	V _{DD} =2.5V	-	0.6	1.2	mA
			V _{DD} =3.3V	-	0.8	1.6	mA
			V _{DD} =5.0V	-	1.0	2.0	mA
		Measurement cct 1, 5009AL3-C-V(f ₀ /4),no load INH=open,f ₀ =24MHz f _{OUT} =6MHz	V _{DD} =2.5V	-	0.6	1.3	mA
			V _{DD} =3.3V	-	0.7	1.5	mA
			V _{DD} =5.0V	-	0.8	1.6	mA
		Measurement cct 1, 5009AL4-C-V(f ₀ /8),no load INH=open,f ₀ =24MHz f _{OUT} =3MHz	V _{DD} =2.5V	-	0.4	0.8	mA
			V _{DD} =3.3V	-	0.5	1.0	mA
			V _{DD} =5.0V	-	0.6	1.2	mA
		Measurement cct 1, 5009AL5-C-V(f ₀ /16),no load INH=open,f ₀ =24MHz f _{OUT} =1.5MHz	V _{DD} =2.5V	-	0.4	0.8	mA
			V _{DD} =3.3V	-	0.4	0.8	mA
			V _{DD} =5.0V	-	0.5	1.0	mA
		Measurement cct 1, 5009AL6-C-V(f ₀ /32),no load INH=open,f ₀ =24MHz f _{OUT} =0.75MHz	V _{DD} =2.5V	-	0.4	0.8	mA
			V _{DD} =3.3V	-	0.4	0.8	mA
			V _{DD} =5.0V	-	0.5	1.0	mA
		Measurement cct 1, 5009AL6-C-V(f ₀ /32),no load INH=open,f ₀ =24MHz f _{OUT} =0.375MHz	V _{DD} =2.5V	-	0.4	0.8	mA
			V _{DD} =3.3V	-	0.4	0.8	mA
			V _{DD} =5.0V	-	0.5	1.0	mA
I _{ST}	Standby current	Measurement cct1, INHN=LOW		-	-	10	uA
R _{UP1}	INH pull-up resistance	Measurement cct6		0.4	1.5	8	MΩ
R _{UP2}				30	70	150	KΩ
R _f	Oscillator feedback resistance	-		70	100	140	KΩ
C _G	Oscillator capacitance	Design value(a monitor pattern on a wafer is tested),Excluding parasitic capacitance		4.8	6	7.2	pF
C _D				8	10	12	pF

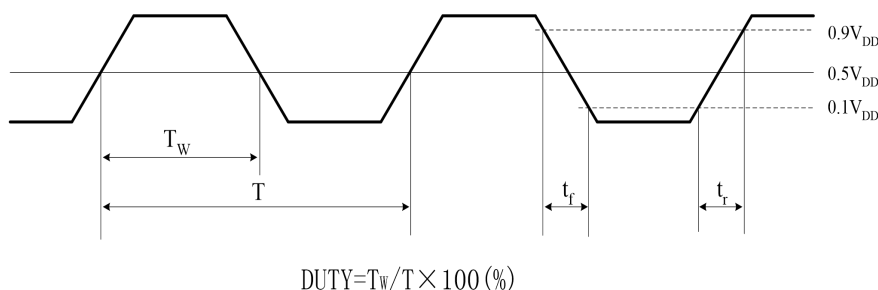


AC Electrical Characteristics

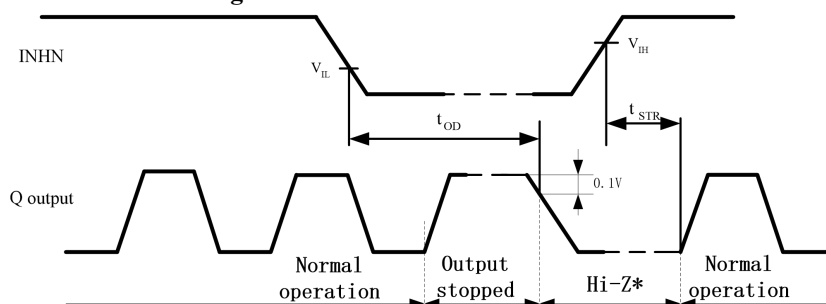
XO5009ALx-C-V Series ($V_{DD}=2.2$ to 5.5 , $T_A=-45$ to 85°C unless otherwise noted)

Parameter	Symbol	Condition		Min	Type	Max	Unit
Output rise time	t _{r1}	Measurement cct1, CL=15pf, 0.1V _{DD} to 0.9V _{DD}	V _{DD} =2.97 to 3.63 V	-	3.0	5.0	ns
	t _{r2}		V _{DD} =4.5 to 5.5V	-	2.0	3.0	ns
Output fall time	t _{f1}	Measurement cct1, CL=15pf, 0.1V _{DD} to 0.9V _{DD}	V _{DD} =2.97 to 3.63V	-	3.0	5.0	ns
	t _{f2}		V _{DD} =4.5 to 5.5V	-	2.0	3.0	ns
Output rise time	t _{r1}	Measurement cct1, CL=50pf, 0.1V _{DD} to 0.9V _{DD}	V _{DD} =2.97 to 3.63V	-	5.0	10	ns
	t _{r2}		V _{DD} =4.5 to 5.5V	-	4.0	8	ns
Output fall time	t _{f1}	Measurement cct1, CL=50pf, 0.1V _{DD} to 0.9V _{DD}	V _{DD} =2.97 to 3.63V	-	5.0	10	ns
	t _{f2}		V _{DD} =4.5 to 5.5 V	-	4.0	8	ns
Output duty cycle	Duty	Measurement cct 1, T _A =25°C,C _L =15pF		45	50	55	%
Output disable delay time	t _{OD}	Measurement cct 1, T _A =25°C,C _L ≤15pF		-	-	50	us

Output switching waveform



Output disable and oscillation start timing chart



When INHN goes HIGH to LOW, the Q output goes HIGH once and then becomes high impedance.

When INHN goes LOW to HIGH, the Q output from high impedance to normal output operation when the oscillation starts (oscillation is detected)

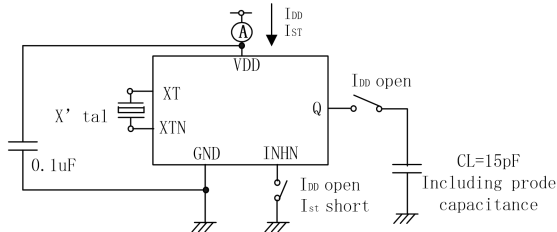
*: the high -impedance interval in the figure is shown as a LOW level due to the $1\text{K}\Omega$ pull-down resistor connected to the Q pin(see“Measurement circuit 2”in the “Measurement circuits” section)



Measurement Circuit

Measurement cct1

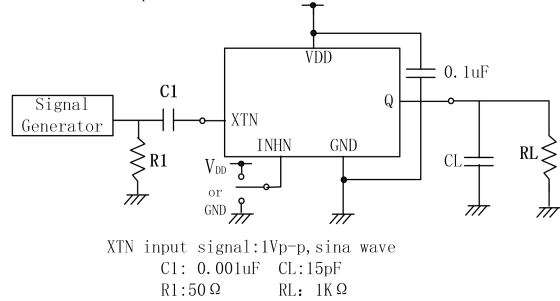
Measurement parameter: I_{DD} , I_{ST} , Duty, t_r , t_f



Note: The AC characteristics are observed using an oscilloscope on pin Q

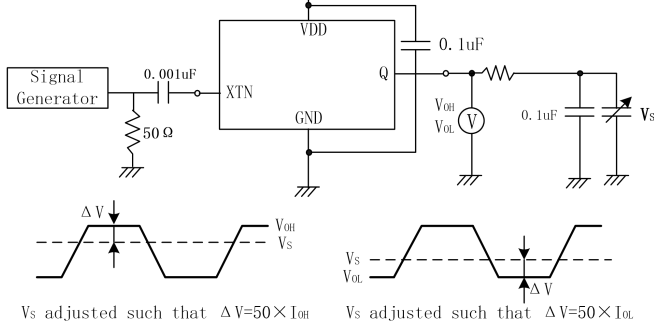
Measurement cct2

Measurement parameter: t_{DD}



Measurement cct3

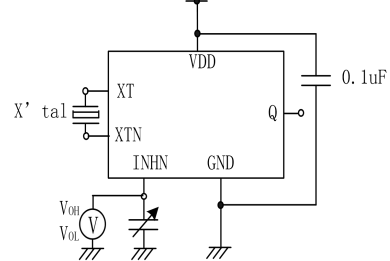
Measurement parameter: V_{OH} , V_{OL}



XTN input signal: 1Vp-p, sine wave

Measurement cct4

Measurement parameter: V_{IH} , V_{IL}



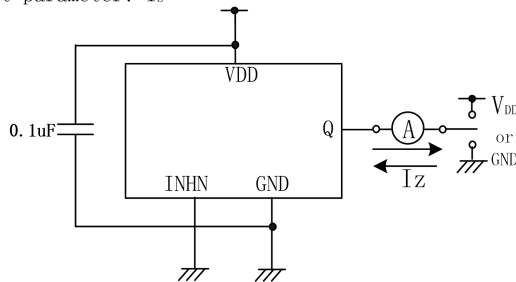
V_{IH} : Voltage is 0V to V_{DD} transition that changes the output state.

V_{IL} : Voltage is V_{DD} to 0V transition that changes the output state.

INHN has an oscillation stop function

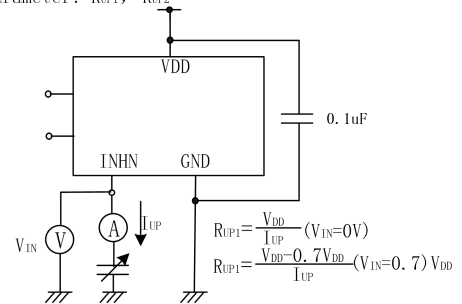
Measurement cct5

Measurement parameter: I_Z



Measurement cct6

Measurement parameter: R_{UP1} , R_{UP2}





Revision History

Revision	Description	DATE
V1.0	Official release	2025/12/23